

Giant magnetic anisotropy changes in $\text{Sr}_2\text{CrReO}_6$ thin films on BaTiO_3

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Abstract

The integration of ferromagnetic and ferroelectric materials into hybrid heterostructures yields multifunctional systems with improved or novel functionality. We here report on the structural, electronic and magnetic properties of the ferromagnetic double perovskite $\text{Sr}_2\text{CrReO}_6$, grown as epitaxial thin film onto ferroelectric BaTiO_3 . As a function of temperature, the crystal-structure of BaTiO_3 undergoes phase transitions, which induce qualitative changes in the magnetic anisotropy of the ferromagnet. We observe abrupt changes in the coercive field of up to 1.2 T along with resistance changes of up to 6.5%. These results are attributed to the high sensitivity of the double perovskites to mechanical deformation.

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Composite or hybrid material systems consisting of ferromagnetic (FM) and ferroelectric (FE) compounds have attracted increasing interest over the last years. They provide strong magnetoelectric coupling, making them promising for new storage devices [1, 2, 3]. Moreover, ferromagnetic thin film/ferroelectric substrate heterostructures allow to study the magnetic properties of one and the same ferromagnetic layer under different strain conditions [4, 5, 6, 7, 8]. In this context, ferromagnetic materials with a strong magnetocrystalline coupling are very attractive. Promising materials are ferromagnetic double perovskites [9] such as $\text{Sr}_2\text{CrReO}_6$ (SCRO), which show a giant anisotropic magnetostriction [10] caused by a large orbital moment on the Re site [11]. In addition, SCRO has a Curie temperature of 635 K [12], well above room temperature, and a predicted high spin polarization of 86% [13]. Here we use $\text{Sr}_2\text{CrReO}_6/\text{BaTiO}_3$ (FM/FE) heterostructures to investigate the magnetic and transport properties of SCRO thin films under different strain conditions, making use of the structural phase transitions of BaTiO_3 (BTO) upon temperature variation [14]: Below 393 K, BTO becomes ferroelectric, and its lattice structure changes from cubic to tetragonal. Within the ferroelectric state, the lattice symmetry is further reduced to orthorhombic (below 278 K), and finally to rhombohedral (below 183 K). The dielectric constant, the spontaneous polarization and the lattice constants change abruptly at these phase transitions accompanied by a thermal hysteresis [14]. Our experiments show a giant change of the magnetic anisotropy and huge coercive fields, depending on the substrate induced strain state.

The choice of SCRO/BTO as FM/FE heterostructure is obvious as the deposition of epitaxial SCRO/BTO heterostructures should be straightforward, since the growth of SCRO films with high crystalline and magnetic quality has been demonstrated on SrTiO_3 (STO) substrates, which have similar crystal structure and lattice constants as BTO [15, 16]. The SCRO films used in this study were grown via pulsed laser deposition [17] in a pure oxygen atmosphere of 6.6×10^{-4} mbar and a substrate temperature of 700° C. These parameters were found to be optimal for SCRO on SrTiO_3 [16]. The films were characterized by high resolution x-ray diffraction (HRXRD), magneto transport measurements in a four-point geometry, and SQUID magnetometry. Note that the saturation magnetic field of SCRO exceeds several Tesla [18], so that a determination of the diamagnetic (substrate) contribution to the SQUID signal is difficult. We therefore subtracted a straight line from all $M(H)$ -loops shown below such that the slope of the signal for high fields becomes zero.

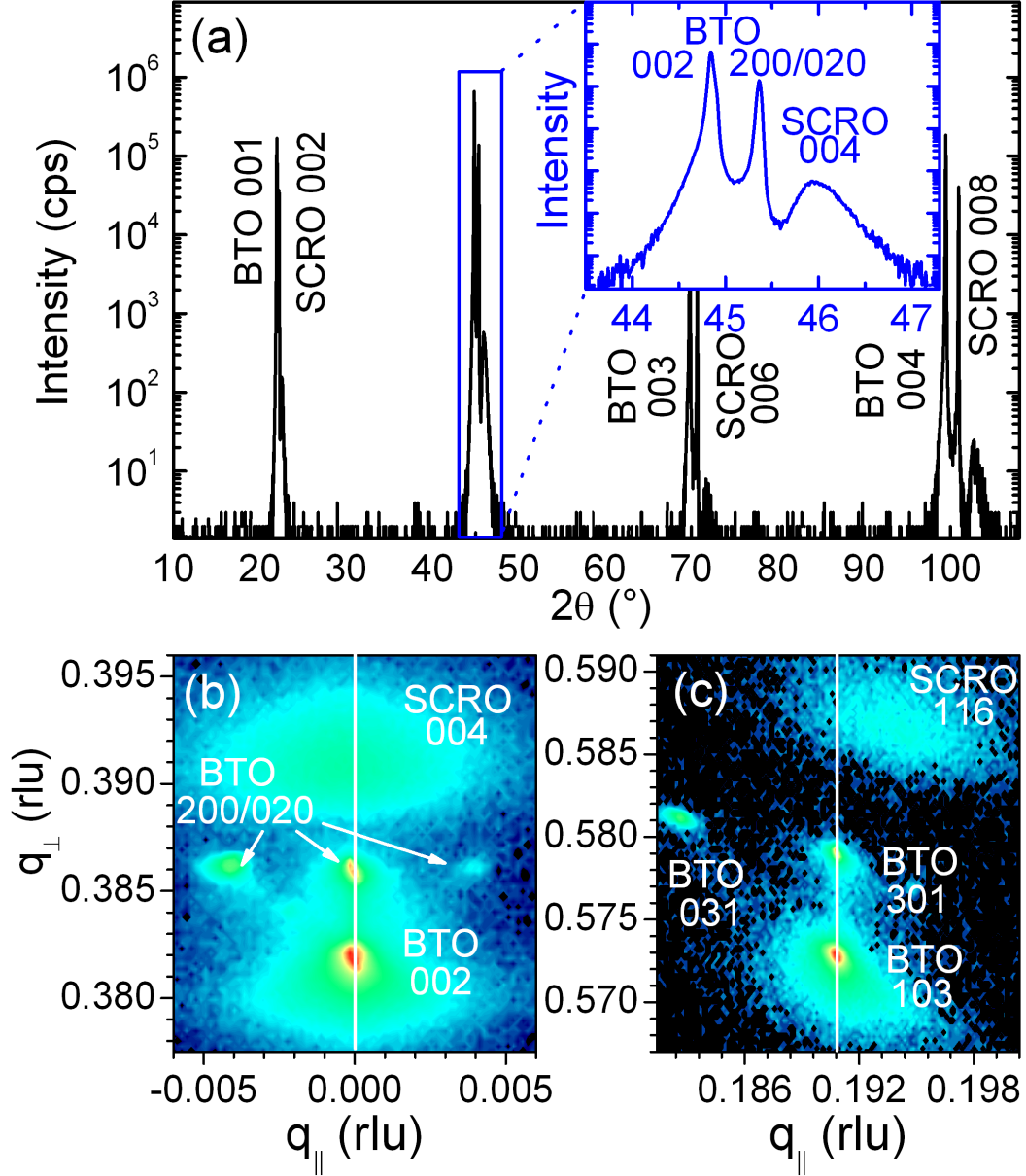


FIG. 1: HRXRD measurement of a 81 nm SCRO film at 310 K with the BTO substrate in the tetragonal phase. (a) ω - 2θ scan. The inset shows the SCRO (004) reflection and the BTO substrate reflection which is split into a -domains (BTO (200)/(020)) and c -domains (BTO (002)). In the main figure only the c -domains are indexed. (b,c) reciprocal space maps around the SCRO (004) and (116) reflections. Clearly the different reflections of the BTO domains are visible.

The structural properties of a 81 nm SCRO film were studied by HRXRD at 310 K, in the tetragonal phase of BTO (Fig. 1). The ω - 2θ scan (Fig. 1(a)) reveals no crystalline parasitic phases in the SCRO film. Moreover, the inset shows the splitting of the BTO substrate reflection due to the presence of different domains in the tetragonal phase (a -domains: BTO (200/020) and c -domains: BTO (002)). A more detailed picture of the structural properties is obtained from the reciprocal space maps (RSM) around the SCRO (004) and SCRO (116) reflections (Fig. 1(b,c)). Clearly no q_{\parallel} -shift of the symmetric (004) SCRO reflection, but a distinct shift of the asymmetric (116) SCRO reflection with respect to the corresponding BTO substrate reflections is observed. This shows that the SCRO film grows c -axis oriented and is partially relaxed with lattice parameters of $a_{\text{SCRO}}=5.614 \text{ \AA}$ and $c_{\text{SCRO}}=7.88 \text{ \AA}$. Moreover, in Fig. 1(b), tilted a -domains with finite q_{\parallel} values are visible. The two classes of a -domains (a_1 : BTO (301) and a_2 : BTO (031)) are clearly seen in Fig. 1(c). Considering the intensities of the reflections from both a - and c -domains, an about equal amount of both domains is found for the present substrate. This multi-domain state of the BTO substrate also results in a considerable mosaic spread, as evident from the full width at half maximum (FWHM) of 0.6° of the rocking curve of the SCRO (004) reflection, which is about one order of magnitude larger than in SCRO films grown on STO [16] and prevents resolving different domains in the SCRO film. Additionally, the presence of a (101) superstructure reflection (not shown) indicates an ordering of the Cr/Re sub-lattice in our SCRO films. From the intensity ratio of the (101) and (404) reflections, the amount of anti-site defects is estimated to be less than 30%.

Whenever the BTO substrate crosses a structural phase transition, the associated change of the lattice parameters should have a substantial effect on the magnetic and electronic properties of the SCRO thin film clamped to its surface [4, 19]. Fig. 2 shows the temperature dependent longitudinal resistivity ρ_{xx} of a 70 nm SCRO film, patterned into a $375 \mu\text{m}$ long and $50 \mu\text{m}$ wide Hall bar. The curves in Fig. 2(a) were measured in an external field of $\mu_0 H=14 \text{ T}$, orthogonal to the film plane, and the ones in Fig. 2(b) at $\mu_0 H=0 \text{ T}$. In both cases, a qualitatively similar $\rho_{xx}(T)$ is observed: Upon cooling the sample from 300 K (black lines), the resistivity increases slightly until it suddenly drops at 285 K, i.e. at the temperature at which the BTO crystal becomes orthorhombic. Between 285 K and 191 K, the resistivity increases again continuously until it jumps to higher values at 191 K, when the BTO transforms into the rhombohedral state. Further cooling leads to a steadily increasing

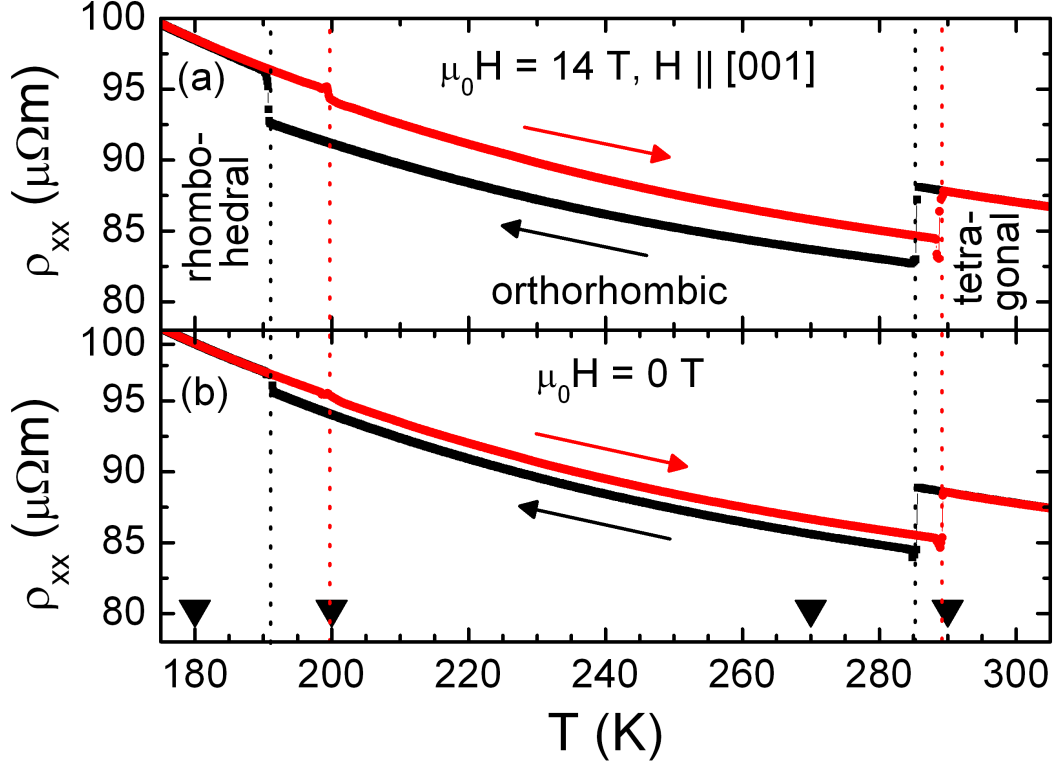


FIG. 2: Temperature dependence of the longitudinal resistivity ρ_{xx} at (a) $\mu_0 H = 14$ T oriented along [001] and (b) 0 T. Jumps in the resistivity at the temperatures of the phase transitions (dotted lines) of the BTO are observed. For the calculation of ρ_{xx} a temperature independent sample length and cross-sectional area was assumed. The black triangles indicate the temperatures at which the magnetization measurements in Fig. 3 were carried out.

resistivity. The red curves in Fig. 2, measured while warming up, reproduce the described behavior with a thermal hysteresis due to the first order phase transitions of the BTO substrate. Please note that the difference in the resistivity for warming and cooling is negligibly small in the rhombohedral and in the tetragonal phase of the BTO substrate. Cracking of the BTO substrate thus is not an issue. Furthermore, the resistivity in these two phases is also very similar for the two magnetic fields $\mu_0 H = 0$ T and 14 T. Only the values in the orthorhombic phase depend strongly on the sweep direction and the magnetic field. Such a dependence was also observed in $\text{La}_{0.5}\text{Sr}_{0.5}\text{MnO}_3$ thin films grown on BTO [19]. Chopdekar *et al.* attributed such a hysteresis to different ratios of *a*- and *c*-domains in the orthorhombic phase depending on whether the previous phase was rhombohedral or tetragonal [20].

The resistivity jumps evident from Fig. 2 are in the range of several percent (up to 6.5%).

Discussing their origin one first has to consider a simple geometry effect due to changes of the length l and the cross-sectional area A of the current path assuming a constant resistivity ρ . Since we did not control the ferroelectric domains in experiment, we also considered a single domain substrate for simplicity. Furthermore, we assumed that the SCRO film volume is conserved and that the film is fully strained. Using the changes of the SCRO lattice constants at the BTO phase transitions [14] we then estimate an upper limit for the expected resistance changes of about 1% for both transitions. This upper bound, as also reported by Lee *et al.*[4], is much smaller than our observations of up to 6.5%. Therefore, a simple geometric effect to explain our data can be ruled out. Anisotropic magnetoresistance effects also should be small, as the magnetization is essentially saturated at an external field of 14 T. On the other hand, it is well known that double perovskites like SCRO are very sensitive towards distortions of the crystal and the corresponding change in the overlap of the orbitals [21]. We therefore attribute the observed resistance jumps to strain induced changes in the orbital configuration of SCRO.

The various crystalline phases of the BTO substrate and the associated change in the orbital configuration should also affect the magnetic properties of the SCRO film. Fig. 3(a) shows the magnetization M versus external magnetic field H , oriented along BTO [100] for four different temperatures: 290 K, 270 K, 200 K, and 180 K. The curves were obtained on a single sample during one cooling cycle. All loops look very similar except for the absolute value of the magnetization at high fields ($|\mu_0 H| > 4$ T). In the tetragonal (crosses) and the rhombohedral phase (full circles) of BTO the M values are nearly identical, whereas in the orthorhombic phase (open circles and triangles) a reduction can be observed. This indicates a reduced saturation magnetization which might be due to the highly twinned BTO crystal in that phase.

In the following we investigate the field dependence of the magnetization in the different BTO phases for three different orientations of the external magnetic field: ip ($H \parallel [100]$), ip45 ($H \parallel [110]$) and oop ($H \parallel [001]$) (see Fig. 3(b)). The temperatures of the field sweeps were chosen slightly above and below the phase transition from tetragonal to orthorhombic (290 K and 270 K) and from orthorhombic to rhombohedral (200 K and 180 K) as indicated by the black triangles in Fig. 2. First we consider the evolution of the in-plane anisotropy. In this case the external magnetic field is applied in the film plane with two orientations: ip (full circles) and ip45 (open circles). In the tetragonal phase of BTO, at 290 K (Fig. 3(c)),

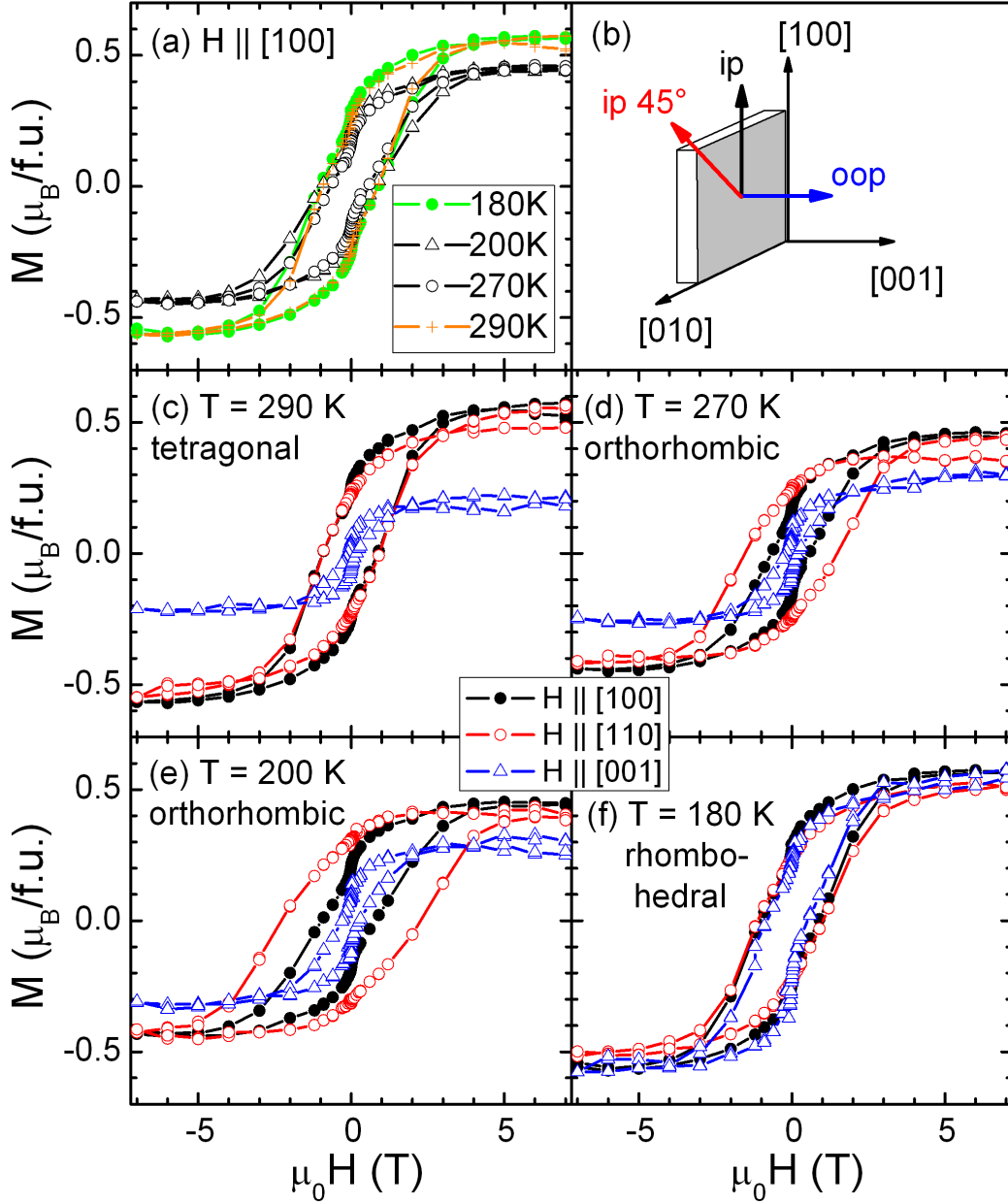


FIG. 3: Magnetization versus external magnetic field. (a) Hysteresis loops at 290 K, 270 K, 200 K and 180 K with the external magnetic field applied along BTO [100]. (b) Illustration of the different orientations of the external field. In panels (c)-(f) hysteresis loops at specific temperatures for different orientations of the external magnetic field are shown.

the two hysteresis loops are very similar. Both show a coercive field of around 0.92 T, and the magnetizations at 7 T are nearly identical ($0.6 \mu_B/f.u.$). This suggests a negligible in-plane magnetic anisotropy. In the orthorhombic phase of BTO, at 270 K and 200 K (Fig.

3(d,e)), the situation is completely different: The coercivities of the ip and ip45 loops differ by more than 1 T. In particular, the hysteresis loops at 200 K reveal a coercive field of 0.87 T for the ip orientation of the external field and a much larger value of 2.3 T for the ip45 orientation. Thus a tremendous in-plane magnetic anisotropy is present. Upon cooling into the rhombohedral phase of BTO (Fig. 3(f)), the situation changes again: The coercive fields and the magnetizations at 7 T for both in-plane hystereses (ip and ip45) as well as the oop loop (open triangles) are nearly identical. In other words, the magnetic behavior appears isotropic, with no evidence of shape or crystalline anisotropy contributions. This is remarkable, as it suggests that giant strain-induced anisotropies of more than 1 Tesla are effective in the SCRO film, compensating demagnetization.

In summary, we have shown that the strain associated with different crystalline phases of a BaTiO₃ substrate induces pronounced changes both in the resistivity and in the magnetic anisotropy of epitaxial Sr₂CrReO₆ thin films. Abrupt jumps of up to 6.5% in the resistivity, as well as tremendous changes in the coercive field of more than 1.2 T were observed as a function of temperature. These observations can be consistently understood considering orbital ordering and the strong electronic correlations in double perovskite ferromagnets.

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